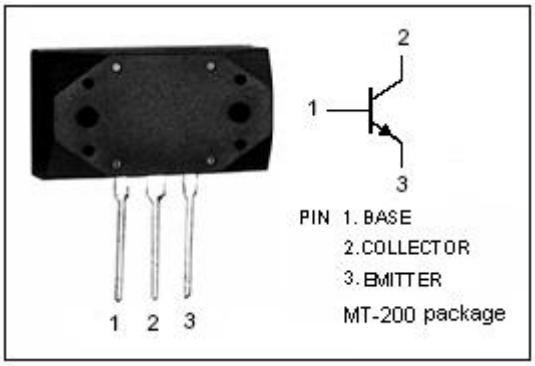
isc Silicon PNP Power Transistor 2SA1494



DESCRIPTION

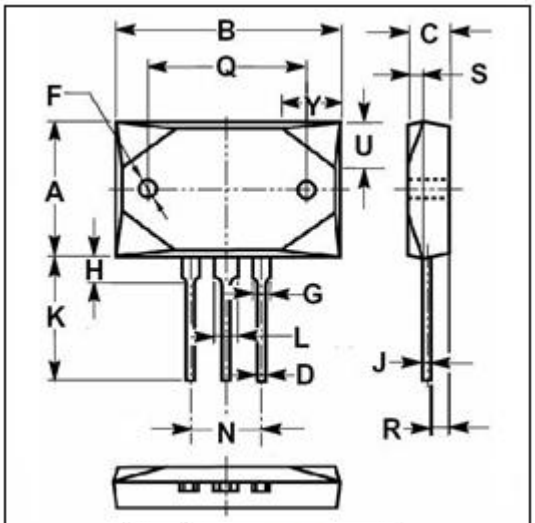
- Collector-Emitter Breakdown Voltage-
  $V_{(BR)CEO}$= -200V(Min)
- Good Linearity of h_{FE}
- Complement to Type 2SC3858
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- For audio and general purpose applications

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-200	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-17	A
I_B	Base Current-Continuous	-5	A
P_C	Collector Power Dissipation @ T_C=25℃	200	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm	
	MIN	MAX
A	20.80	21.20
B	35.50	36.50
C	5.55	5.85
D	0.95	1.05
F	3.30	3.70
G	2.20	2.60
H	3.45	3.85
J	0.55	0.95
K	20.70	21.20
L	2.20	2.60
N	10.40	11.00
Q	24.00	24.50
R	2.60	3.00
S	2.10	2.30
U	6.30	6.70
Y	8.60	9.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -50mA ; I_B= 0	-200			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -10A; I_B= -1A			-2.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -200V ; I_E= 0			-100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -6V; I_C= 0			-100	μA
h_{FE}	DC Current Gain	I_C= -8A ; V_{CE}= -4V	50		180	
C_{OB}	Output Capacitance	I_E= 0 ; V_{CB}= -10V;f_{test}= 1.0MHz		500		pF
f_T	Current-Gain—Bandwidth Product	I_E= 1A ; V_{CE}= -12V		20		MHz
Switching times						
t_{on}	Turn-on Time	I_C= -10A ,R_L= 4Ω , I_{B1}= -I_{B2}= -1A,V_{CC}= -40V		0.6		μs
t_{stg}	Storage Time			0.9		μs
t_f	Fall Time			0.2		μs

h_{FE} Classifications

Y	P	G
50-100	70-140	90-180